TOSHIBA TPD1018F

TOSHIBA INTELLIGENT POWER DEVICE SILICON MONOLITHIC POWER MOS INTEGRATED CIRCUIT

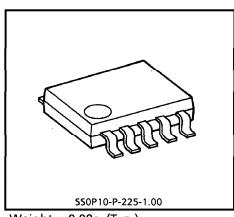
TPD1018F

HIGH-SIDE POWER SWITCH for MOTORS, SOLENOIDS, and LAMP **DRIVERS**

TPD1018F is a monolithic power IC for high-side switches. The IC has a vertical MOS FET output which can be directly driven from a CMOS or TTL logic circuit (eg, an MPU). The device offers intelligent self-protection and diagnostic functions.

FEATURES

- A monolithic power IC with a new structure combining a control block (Bi-CMOS) and a vertical power MOS FET (π -MOS) on a single chip.
- One side of load can be grounded to a high-side switch.
- Can directly drive a power load from a microprocessor.
- Built-in protection against overvoltage, overheating, and load short circuiting
- Incorporates a diagnosis function that allows diagnosis output to be read externally at load short circuiting, overvoltage, or overheating.
- Low on resistance : R_{DS} (ON) = 0.8Ω (Max)
- Low operating current: $I_{DD} = 120 \mu A$ (Typ.), @ $V_{DD} = 13.2 \text{V}$, $V_{IN} = 0$
- 10-pin SSOP package for surface mounting.

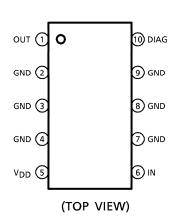


Weight: 0.08g (Typ.)

BLOCK DIAGRAM

BANDGAP REGULATOR O VDD CHARGE PUMP OVER-VOLTAGE DRIVER π -MOS CURRENT SENSE DIAGO THERMAL SHUTDOWN GND O

PIN ASSIGNMENT



(Note) That because of its MOS structure, this product is sensitive to static electricity.

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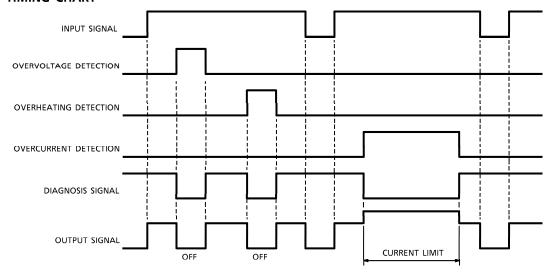
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PIN DESCRIPTION

PIN No.	SYMBOL	FUNCTION			
1	OUT	Output pin. When the load is short circuited and current in excess of the detection current (0.5A min) flows to the output pin, the current limiter operates to protect the IC.			
2, 3, 4	GND	round pins.			
5	v _{DD}	Power pin. Incorporates an overvoltage protection function which turns off the output when the voltage applied exceeds 25V (min). Protects IC and load. Incorporates 2V (typ) hysteresis.			
6	IN	Input is CMOS-compatible, with pull-down resistor connected. Even if the input is open, output will not accidentally turn on.			
7, 8, 9	GND	Ground pins.			
10	DIAG	Self-diagnosis detection pin. Goes low when overcurrent, overheating, or overvoltage is detected. N-channel open drain.			

TIMING CHART



TRUTH TABLE

INOTH TABLE					
INPUT SIGNAL	OUTPUT SIGNAL	DIAGNOSIS OUTPUT	STATE		
Н	Н	Н	Normal		
L	L	Н	Normai		
Н	L	L	Load short		
L	L	Н	circuited		
Н	L	L	Overheating		
L	L	Н	Overneating		
Н	Ĺ	Ĺ	Overvoltage		
L	L	Н	Overvortage		

MAXIMUM RATINGS (Ta = 25° C)

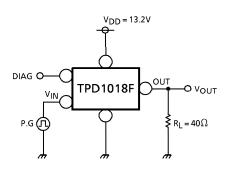
CHARACTERIS	STIC	SYMBOL	RATING	UNIT	
Drain-source Voltage	e	V _{DS}	60	V	
Cumply Valtage	DC	V _{DD} (1)	25	٧	
Supply Voltage	Pulse	V _{DD} (2)	60 (Rs = 1Ω , τ = 250ms)	٧	
Innut Valtana	DC	V _{IN} (1)	-0.5~25	V	
Input Voltage	Pulse	V _{IN} (2)	V _{DD (1)} + 1.5 (t = 100ms)	٧	
Output Current		lo	0.5	Α	
Input Current		liΝ	± 10	mA	
Power Dissipation	Ta = 25°C	PD	300	mW	
Operating Temperat	ng Temperature T _{opr} – 40~125		°C		
Junction Temperatu	re	Tj	150		
Storage Temperatur	е	T _{stg}	- 55∼150	°C	

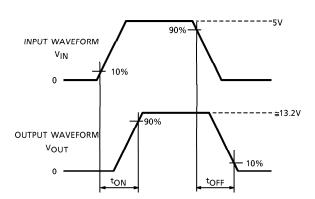
ELECTRICAL CHARACTERISTICS (Tj = $-40 \sim 125$ °C)

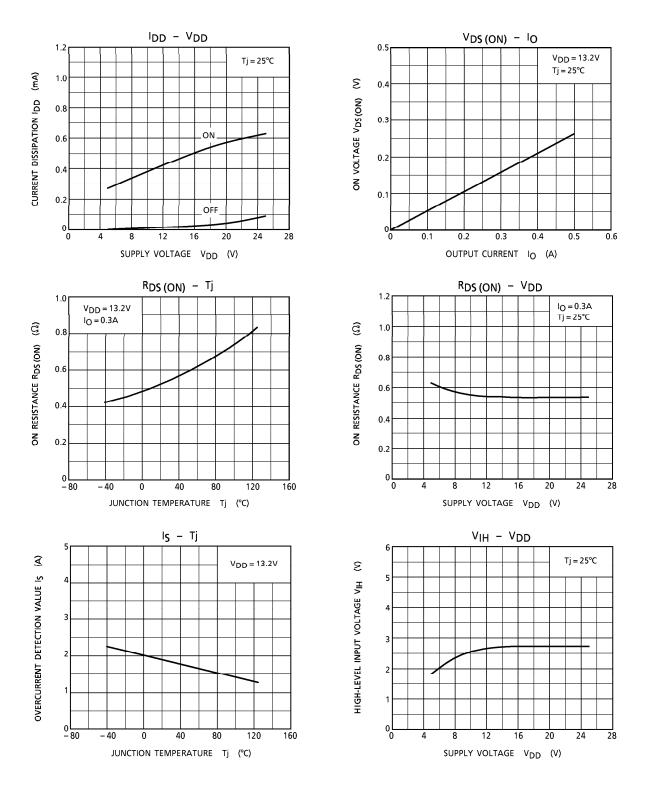
CHARACTERISTIC		SYMBOL	TEST CIR- CUIT	TEST CONDITION	MIN	TYP.	MAX	UNIT
Operating Supply Voltag		V _{DD} (OPR)	<u> </u>	_	5	12	25	V
Current Dissin	Company Dissipation			$V_{DD} = 13.2V, V_{IN} = 0, Tj = 85^{\circ}C$	_	120	300	μΑ
Current Dissipation		IDD (2)	_	$V_{DD} = 13.2V, V_{IN} = 5V$	_	1	1.5	mA
Input Voltage		V _{IH}	_	$V_{DD} = 13.2V, I_{O} = 300mA$	3.5	_	_	٧
		V _{IL}	_	$V_{DD} = 13.2V, I_{O} = 100 \mu A$	1		1.5	V
Input Current		^I IN (1)		$V_{DD} = 13.2V, V_{IN} = 5V$	1	10	100	μ A
		I _{IN} (2)		$V_{DD} = 13.2V, V_{IN} = 0$	- 0.2		0.2	μ A
On Voltage		V _{DS} (ON)	_	$V_{DD} = 13.2V, I_{O} = 300 \text{mA},$ Tj = 25°C		0.21	0.24	\ \
On Resistance		R _{DS} (ON)(1)	-	$V_{DD} = 13.2V, I_{O} = 300 \text{mA},$ Tj = 25°C		0.7	0.8	Ω
		R _{DS} (ON)(2)		$V_{DD} = 13.2V$, $I_{O} = 300$ mA, $T_{j} = -40 \sim 85$ °C	I	l	1.2	Ω
Diagnosis Output "L" Level			_	V _{DD} = 13.2V, I _{DL} = 1mA	ı	ı	0.4	>
Diagnosis Out Current	put "H" Lev	el I _{DH}	_	V _{DD} = 25V, I _{DH} = 25V	l	l	10	μΑ
Output Leakage Current		loL		$V_{DD} = 25V, V_{IN} = 0$			100	μ A
Overcurrent P	rotection	lς	_	$V_{DD} = 13.2V, Tj = 25^{\circ}C$	0.5		3	Α
Overheating	Temperatui	e T _S		_	150	160	200	°C
Protection	Hysteresis	∆TS			l	20	50	°C
Overvoltage	Voltage	V _{DDS}		_	25		_	V
Protection	Hysteresis	△V _{DDS}		_	_	2	7	V
Switching Time		ton	1	V_{DD} = 13.2V, R_L = 40 Ω	_	50	_	μs
		tOFF		Tj = 25°C	_	10	_	μ s

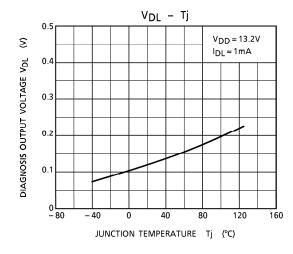
TEST CIRCUIT 1

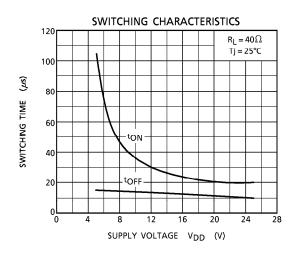
Switching Time

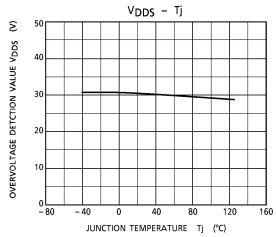


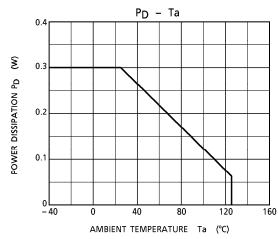












PRECAUTION:

- 1. Since protection for, for example, reverse connection of the battery is not incorporated, provide protection using external circuits.
- 2. Since a negative bias protection circuit for the output pin is not incorporated, when negative bias is applied to the output pin, connect a freewheeling diode (FWD) between OUT and GND.

OUTLINE DRAWING SSOP10-P-225-1.00 Unit : mm 0.6TYP 1.0 5.7MAX 5.2±0.2 7.0+4-0.1 0.525±0.2

Weight: 0.08g (Typ.)